Current Pending claims:

Clean copy of Pending Claims as filed in Response to Office Action dated June 19, 2002:

1.(Amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of and on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of from ~$6x10^{19}$ cm^{-3} to ~[3.75] $1x10^{20}$ cm^{-3} and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coefficients are opposite each other.

2.(Amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of less than ~$3.75x10^{20}$ cm^{-3} and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coeffients are opposite each other.

11.(Amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a dopng wherein said doping has a concentration of greater than ~$6x10^{19}$ cm^{-3} and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coefficients are opposite each other.

12.(Amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a late implant doping technique and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coefficients are opposite each other.